YJB5D0G06HQ

$_{\text{DS}}$ Tested

General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free
- Part no. with suffix ”Q” means AEC-Q101 qualified

Applications

- Power switching application
- Uninterruptible power supply
- DC-DC convertor

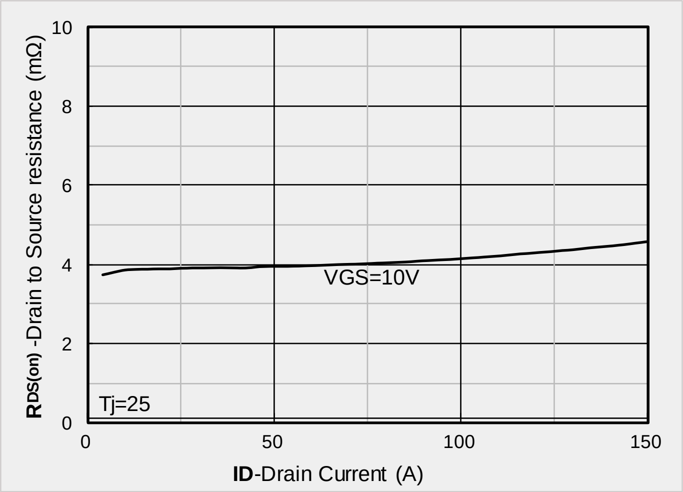
■ **Absolute Maximum Ratings** (T_J=25 unless otherwise noted)

Parameter

■ Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						

YJB5D0G06HQ



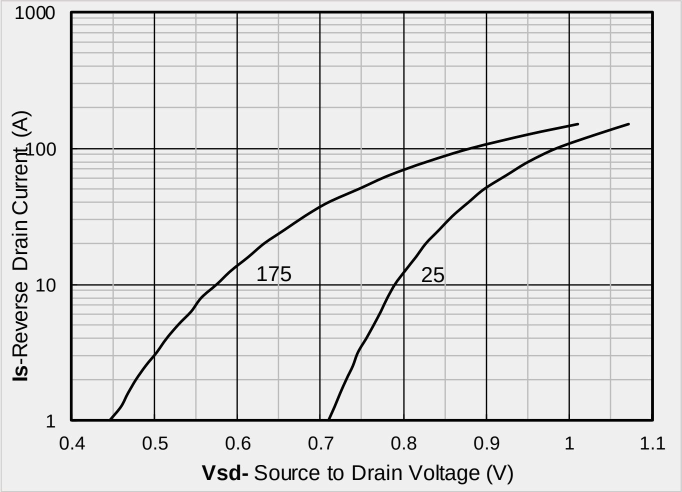
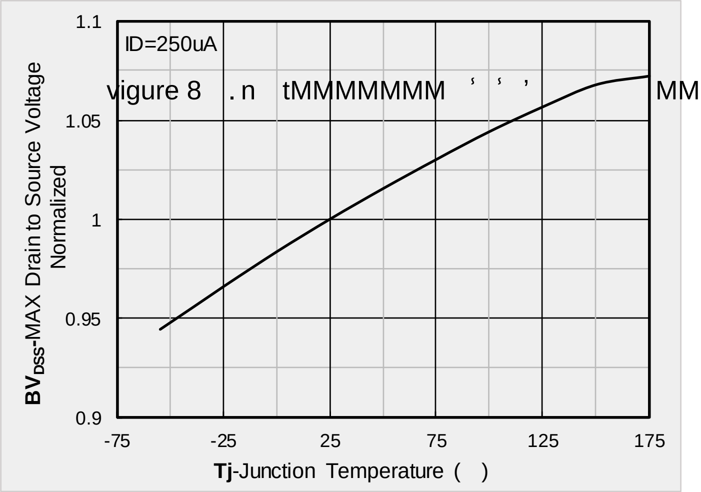
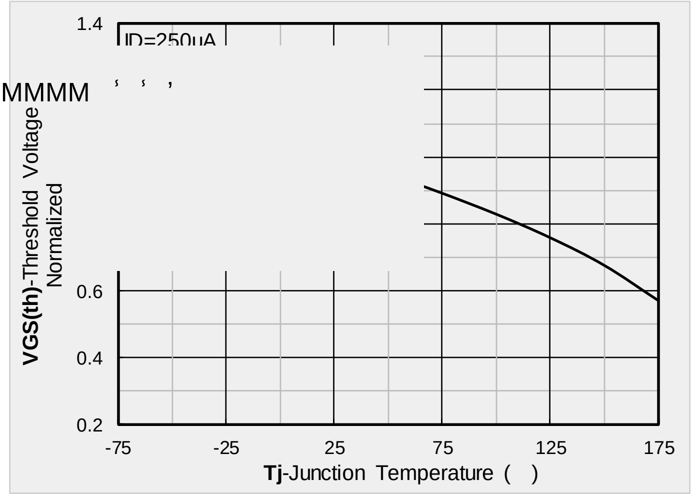


Figure 7. RDS(on) VS Drain Current

Figure 8. Forward characteristics of reverse diode





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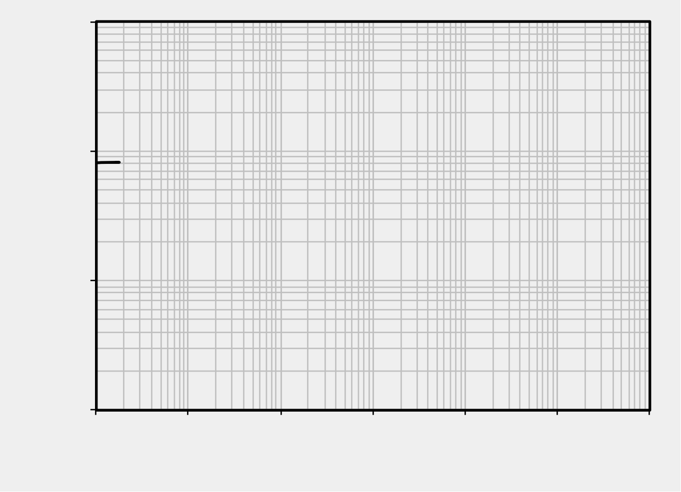

■ TO-263-HY Package information

SYMBOL	MIN.	
	0.000	
A2	0.174	0.180
b2		0.050
c		
c2		
D2		
E		
E1		

'LVFODLPHU

7KH LQIRUPDWLRQ SUHVHQWHG LQ WK\LV< DQJ]KRX <DQJMLH (OHFWURQLF 7HFKQRO
ULJKW WR PDNH FKDQJHV WR WKH SURGXFW ZLWKRXW QRWLFH RU WR GLVFRQWLQXH DQ\ SURGXFW GHVFULEHG KHUHLQ ZLWKRXW QRWLFH
RWKHUZLVH

7KH SURGXFW OLVWLQJV FRQWDLQHG KHUHLQ DUH QRW LQWHQGHG IRU XVH LQ PHGLFDO OLIH
VDYLQJ OLIHVXVWDLQLQJ DSSOLFDWLRQV RU RWKHU DSSOLFDWLRQV ZKHUH IDLOXUH FRXOG UHVXOW LQ SHUVRQDO LQMXU\
VXFK LPSURSHU XVH RI VDOH

7KLV SXEOLFDWLRQ VXSHUVHGHV DQG UHSODFHV DOO LQIRUPDWLRQ SUHYLRXVO\ VXSSOLHG
ZZZ \DQJMLH FRP RU FRQVXOW \RXU QHDUHVW VDOHV UHSUHVHQWDWLYH